



PRODUCT DATA SHEET



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Datasheet



Resources



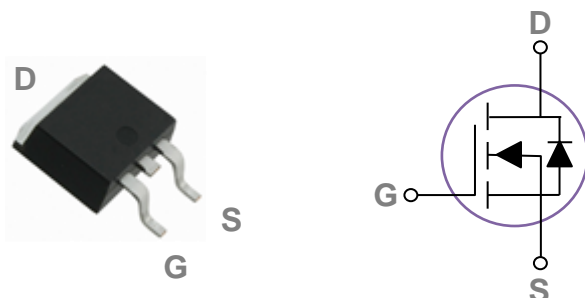
Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

TO252 Pin Configuration



BVDSS	RDSON	ID
30V	4.1mΩ	74A

Features

- 30V, 74A, $R_{DS(ON)} = 4.1\text{m}\Omega @ V_{GS} = 10\text{V}$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C=25^\circ\text{C}$)	74	A
	Drain Current – Continuous ($T_C=100^\circ\text{C}$)	46.8	A
I_{DM}	Drain Current – Pulsed ¹	296	A
EAS	Single Pulse Avalanche Energy ²	115	mJ
IAS	Single Pulse Avalanche Current ²	48	A
P_D	Power Dissipation ($T_C=25^\circ\text{C}$)	54.3	W
	Power Dissipation – Derate above 25°C	0.44	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.3	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.03	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =15A	---	3.4	4.1	mΩ
		V _{GS} =4.5V, I _D =10A	---	4.7	6	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.6	2.5	V
△V _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.17	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	---	10	---	S

Dynamic and switching Characteristics

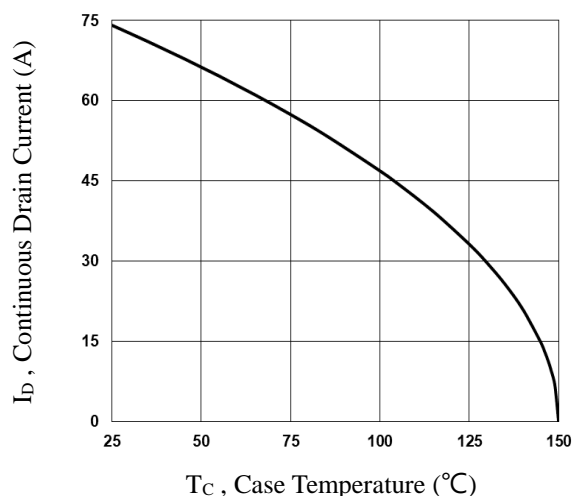
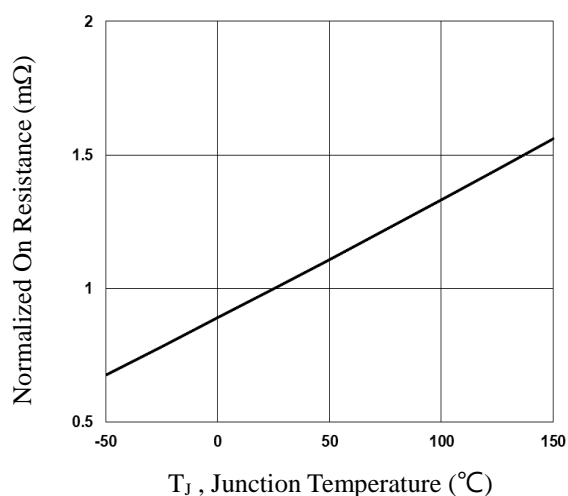
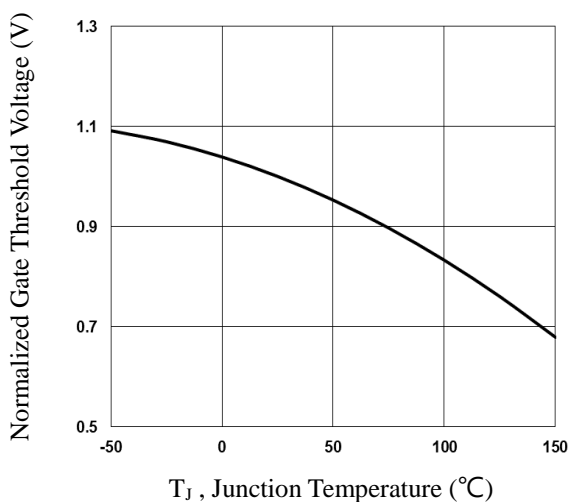
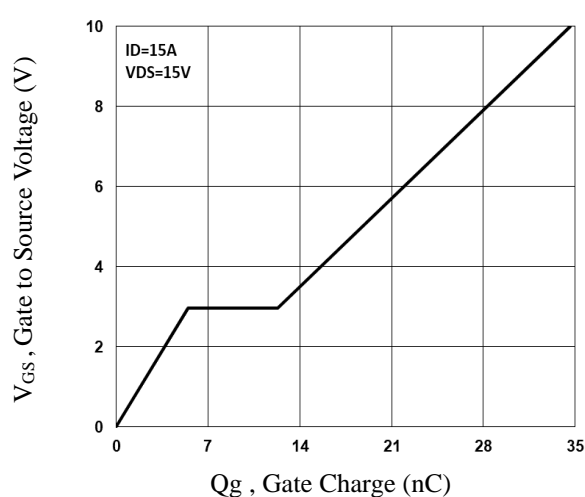
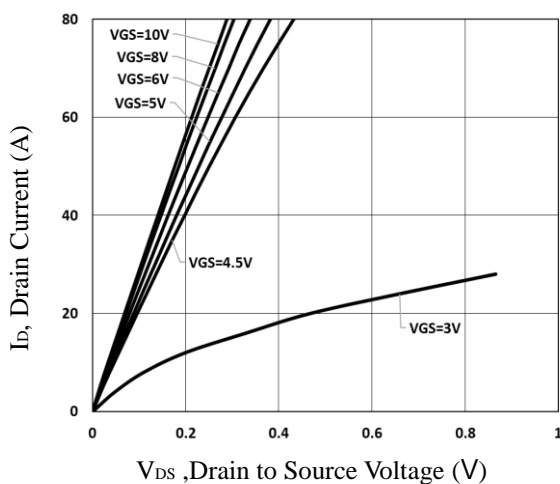
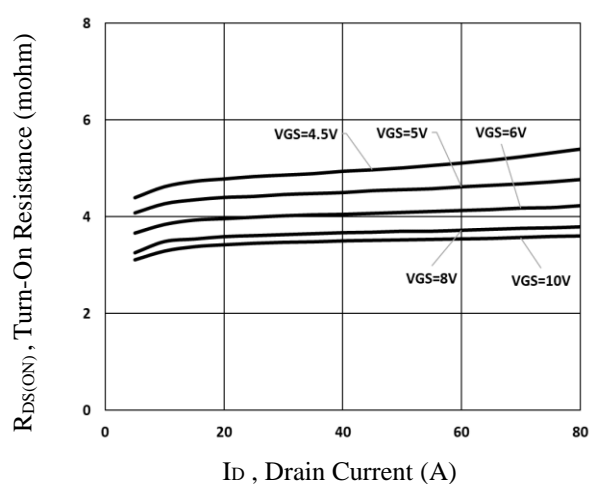
Q _g	Total Gate Charge ^{3, 4}	V _{DS} =15V, V _{GS} =10V, I _D =15A	---	34.6	70	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	5.5	11	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	6.8	13	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	9.7	20	ns
T _r	Rise Time ^{3, 4}		---	15.8	31	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	37.4	75	
T _f	Fall Time ^{3, 4}		---	12	24	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, F=1MHz	---	1910	3800	pF
C _{oss}	Output Capacitance		---	300	600	
C _{rss}	Reverse Transfer Capacitance		---	230	460	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.14	---	Ω

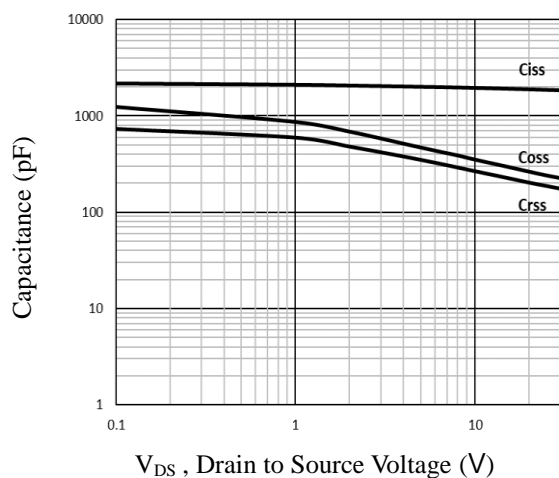
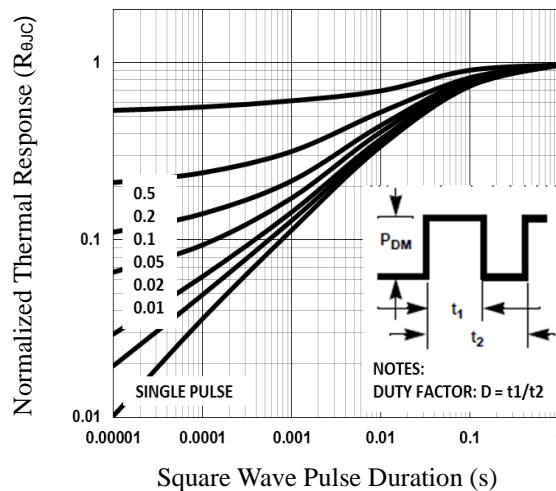
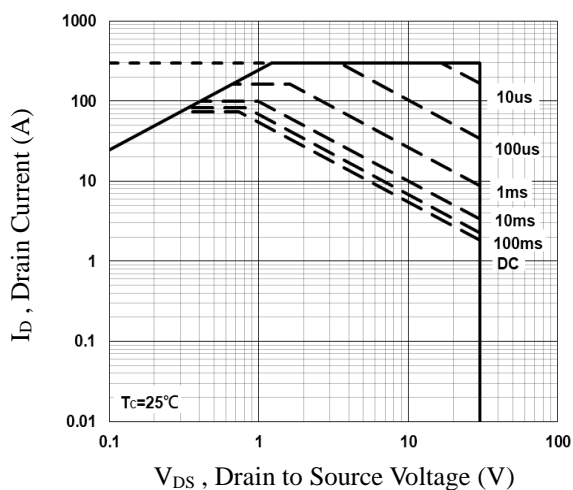
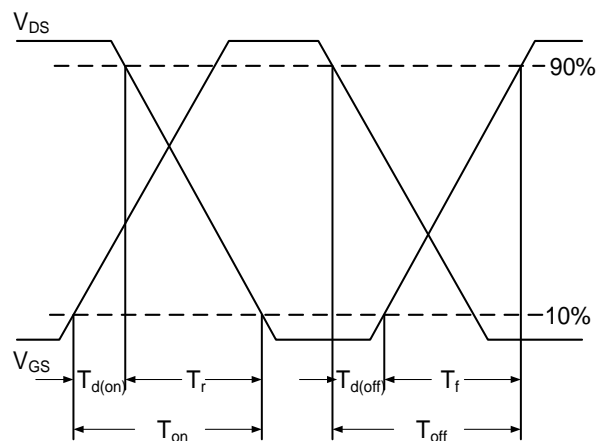
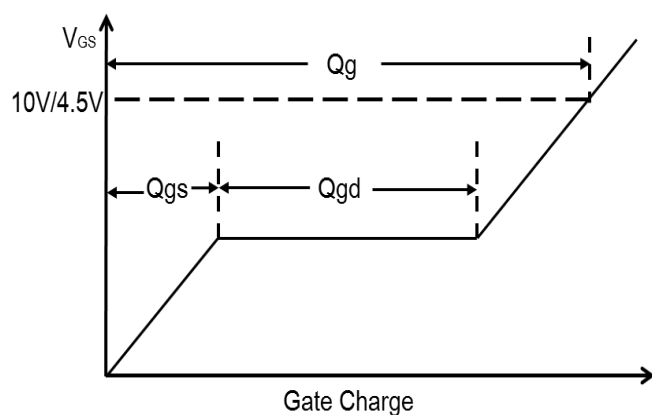
Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	74	A
I _{SM}	Pulsed Source Current		---	---	148	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{DS} =30V, I _S =10A, di/dt=100A/μs	---	2.33	---	us
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	48.9	---	uC

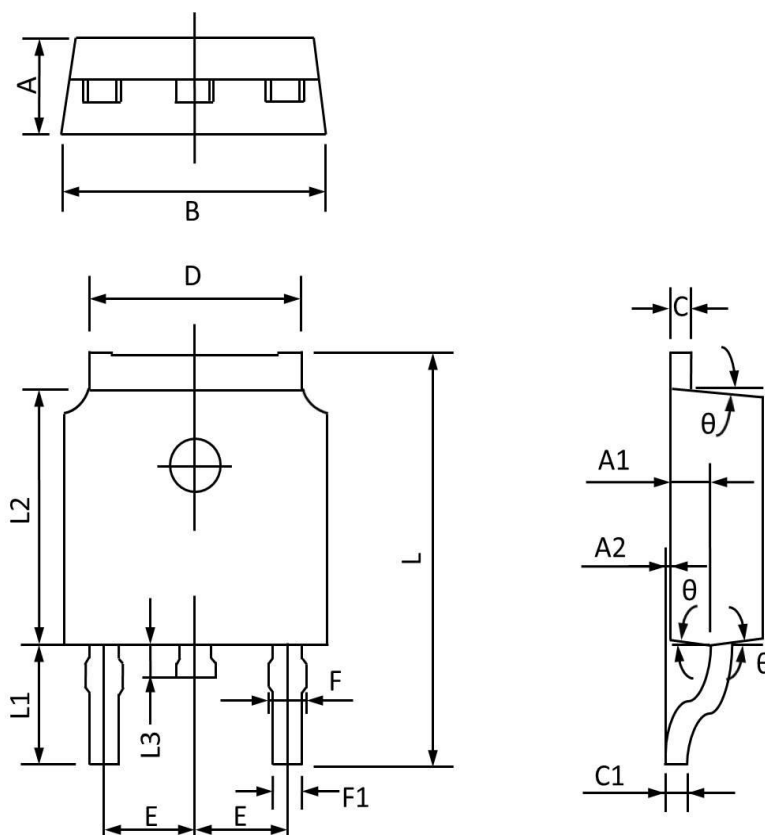
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=48A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.


Fig.1 Continuous Drain Current vs. TC

Fig.2 Normalized RDSON vs. TJ

Fig.3 Normalized V_{th} vs. T_J

Fig.4 Gate Charge Characteristics

Fig.5 Typical Output Characteristics

Fig.6 Turn-On Resistance vs. I_D


Fig.7 Capacitance Characteristics

Fig.8 Normalized Transient Impedance

Fig.9 Maximum Safe Operation Area

Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform

TO252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.400	2.200	0.094	0.087
A1	1.110	0.910	0.044	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.400	0.268	0.252
C	0.580	0.450	0.023	0.018
C1	0.580	0.460	0.023	0.018
D	5.500	5.100	0.217	0.201
E	2.386	2.186	0.094	0.086
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.400	0.244	0.213
L3	1.200	0.600	0.047	0.024
θ	9°	3°	9°	3°

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